

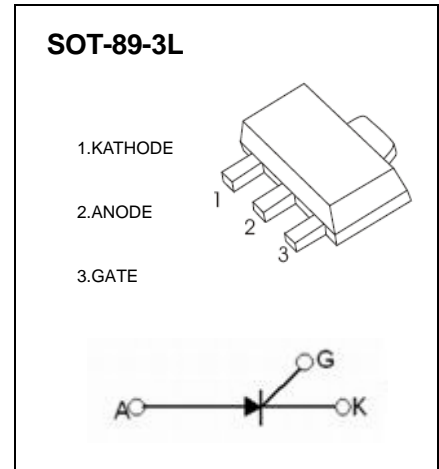


SOT-89-3L Plastic-Encapsulate Thyristors

MCR100- 6,- 8 Silicon Controlled Rectifier

FEATURES

- Current- I_{GT} : 200 μ A
- I_{TRMS} : 0.8 A
- V_{RRM}/V_{DRM} : MCR100-6: 400 V
MCR100-8: 600 V
- Operating and storage junction temperature range
 T_J, T_{stg} : -55°C to +150°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage	V_{TM}^*	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage MCR100-6 MCR100-8	V_{DRM} AND V_{RRM}	$I_{DRM}= 10 \mu A$	400 600		V	
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}= \text{Rated}$ V_{DRM} or V_{RRM}		10	μA	
Holding current	I_H	$I_{HL}= 20mA, V_{AK} = 7V$		5	mA	
Gate trigger current	I_{GT}	$V_{AK}=7V$	A2	5	15	μA
			A1	15	30	μA
			A	30	80	μA
			B	80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.